

Rev.F May.-2019

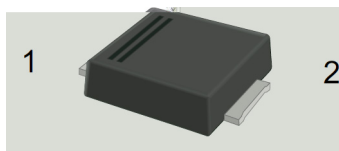
50V~600V 2.0A SMBF

Surface Mount Superfast Recovery Rectifier, Reverse Voltage: 50 to 600V, Forward Current: 2.0A, SMBF thin package.

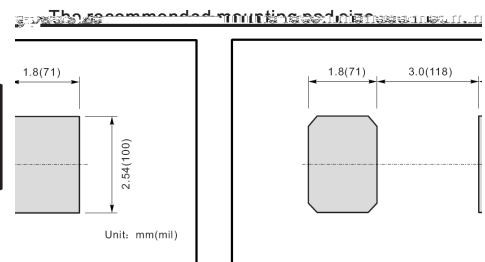
RoHS 2011/65/EU

Glass Passivated Chip Junction, Fast reverse recovery time, Lead free in comply with EU RoHS 2011/65/EU directives, For surface mounted applications, Halogen free product.

General purpose.



PIN	DESCRIPTION
1	Cathode
2	Anode



See Marking Instructions.

Rev.F May.-2019

Parameter	Symbol	Rating							Unit
		ES2ABF	ES2BBF	ES2CBF	ES2DBF	ES2EBF	ES2GBF	ES2JBF	
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	150	200	300	400	600	V
Maximum RMS voltage	V_{RMS}	35	70	105	140	210	280	420	V
Maximum DC Blocking Voltage	V_{DC}	50	100	150	200	300	400	600	V
Maximum Average Forward Rectified Current at $T_L = 100$	$I_{F AV}$	2.0							A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	50							A
Typical Junction Capacitance at $V_R = 4V$, $f = 1MHz$	C_j	45							pF
Typical Thermal Resistance ¹	$R_{\theta JA}$	65							/W
Operating and Storage Temperature Range	T_j, T_{stg}	-55~+150							

Note:

1 P.C.B. mounted with 0.5 X 0.5" (12.7 X 12.7 mm) copper pad areas.

Parameter	Symbol	Test Conditions	Rating							Unit
			ES2ABF	ES2BBF	ES2CBF	ES2DBF	ES2EBF	ES2GBF	ES2JBF	
Maximum Forward Voltage	V _F	I _F =2.0A	1.0				1.25		1.65	V
Maximum DC Reverse Current at Rated DC Blocking Voltage	I _R	T _a =25	5.0							μA
		T _a =125	100							μA
Maximum Reverse Recovery Time	t _{rr}	I _F =0.5A I _R =1.0A I _{rr}								

Ō ? d • Ž ¢ / Electrical Characteristic Curve

, M y f / Marking Instructions

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^a¢y

10• Ä ½ “ † 150 ½180 - k ž • 60 ½90sec;

20• Q > “ † 245 r5 - k ž • 4 Ò 5 r

Note:

1.Preheating:150~180 - , Time:60~90sec.